

BCR602 hot plug IC with dimming

60 V linear LED controller IC for dimmable LED applications with ripple suppression, overtemperature and hot plug protection

Features

- Supply voltage 8 V to 60 V,
- Supports use of NPN bipolar transistors and NMOS MOSFETS,
- AC supply voltage ripple suppression,
- Dimming at pin *MFIO*
 - 3% analog dimming of LED current by resistor R_{set} or DC voltage,
 - 1% PWM dimming of LED current by PWM signals,
- R_{set} functionality at pin *MFIO*,
- LED current precision $\pm 3\%$.



Protection features

- Hot plug protection,
- Overtemperature protection.

Target applications

- LED light engines/modules,
- LED replacement lamps.

Advantages with respect to discrete solutions

- Low BOM count,
- Lower assembly cost,
- Smaller form factor,
- Higher reliability due to less parts and soldering joints.

Product validation

Qualified for industrial applications according to the relevant tests of JEDEC47/20/22.

Device information

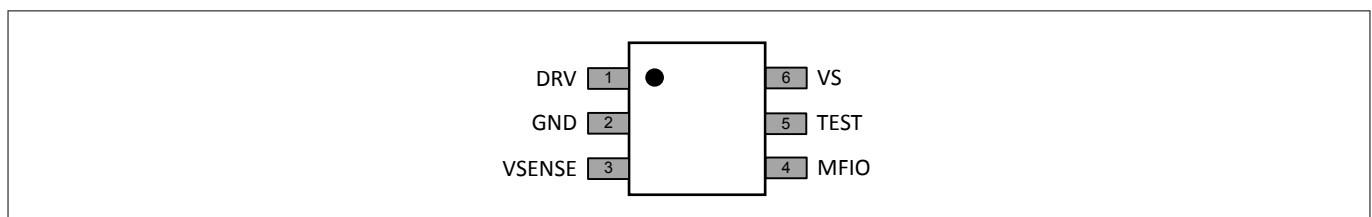


Figure 1 Pin configuration

Description

Table 1 **Part information**

| Type | Package | Configuration | Marking code |
|--|------------|---------------|--------------|
| 60V Linear Current Control Chip BCR602 | PG-SOT23-6 | n.a. | 602 |

Description

BCR602 is a linear LED controller IC regulating the LED current by means of an external driver transistor. BCR602 supports use of NPN bipolar transistors and NMOSFETs to cover a wide LED current and power range up to several hundred mA. The LED current is fully scalable by dimensioning an external current sense resistor. BCR602 suppresses the voltage ripple of the power supply driving a constant LED current for better light quality. The LED current can be dimmed by resistors as well as analog or digital PWM voltages connected to the Multi Function Input Output (MFIO) pin. The embedded hot plug protection allows plug in and plug out of any LED load during operation.

The overtemperature protection will dim the LED current if the BCR602 junction temperature threshold is exceeded. In this case the LED current will be reduced to 30% of the nominal current. Once the junction temperature drops below the temperature hysteresis nominal LED current is resumed.

The BCR602 is a perfect fit for LED applications by combining small form factor with low cost. Through its higher integration, BOM savings and ensuring long lifetime of LEDs, this controller has many advantages compared to discrete solutions.

Table of contents

| | | |
|----------|--|----|
| | Features | 1 |
| | Protection features | 1 |
| | Target applications | 1 |
| | Advantages with respect to discrete solutions | 1 |
| | Product validation | 1 |
| | Device information | 1 |
| | Description | 2 |
| | Table of contents | 3 |
| 1 | Pin configuration | 4 |
| 2 | Functional description | 5 |
| 3 | Thermal characteristics | 7 |
| 4 | Absolute maximum ratings | 8 |
| 5 | Operating conditions | 9 |
| 6 | Electrical characteristics | 10 |
| 7 | Package information | 13 |
| 8 | References | 14 |
| | Revision history | 14 |
| | Disclaimer | 15 |

Pin configuration

1 Pin configuration

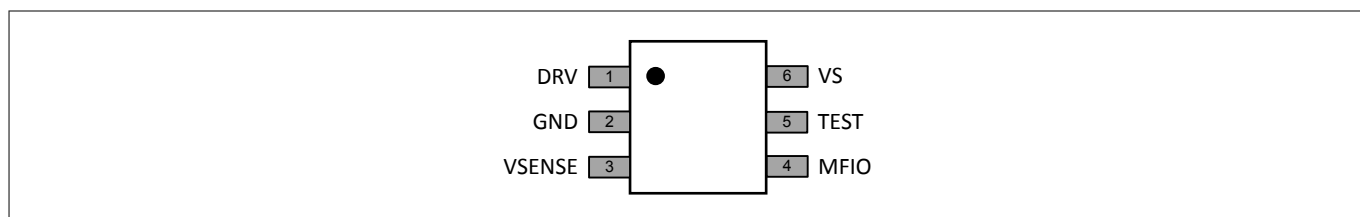


Figure 2 Pin configuration

Table 2 Pin configuration

| Pin no. | Pin name | Pin type | Function |
|---------|---------------|----------|--|
| 1 | <i>DRV</i> | Output | Driver output to control base or gate of the external transistor |
| 2 | <i>GND</i> | GND | IC ground |
| 3 | <i>VSENSE</i> | Input | Measurement of V_{sense} voltage |
| 4 | <i>MFIO</i> | Input | Multifunctional IO for resistive (via external R_{set}), DC voltage and PWM voltage dimming |
| 5 | <i>TEST</i> | Output | For test purpose, it must not be directly connected to ground. It is recommended to leave <i>TEST</i> pin open or attach a resistor to ground > 1 M Ω . |
| 6 | <i>VS</i> | Input | Supply voltage |

Functional description

2 Functional description

Typical application circuit

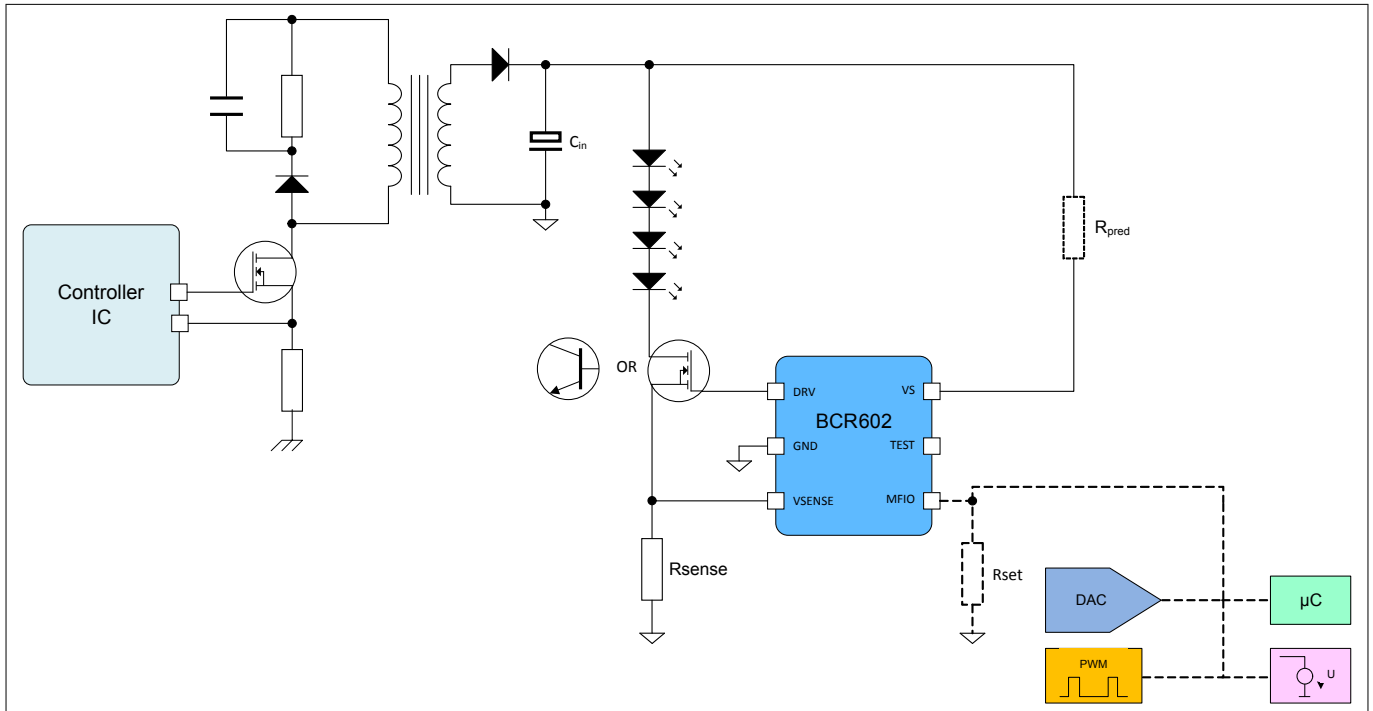


Figure 3 Typical application circuit

Application hints

1. External driver transistors
BCR602 is able to drive NPN transistors as well as NMOSFETs. NPN transistors can be used for LED currents up to several 100 mA while NMOSFETs are preferable for high LED currents. The smaller current using BJTs is caused by the DC current gain value h_{FE} value of the used BJT. E.g. a typical h_{FE} of 75 limits the application to a maximum below 750 mA.
2. Supply voltage of BCR602
To drive higher output currents into an external NPN driver transistor it might be necessary to limit the supply voltage of BCR602 significantly below 60 V to reduce power dissipation inside the IC. This can be achieved either by adding a series resistor (R_{pred}) between supply voltage and VS pin of BCR602 or by operating BCR602 by an auxiliary winding of the power supply providing a lower IC supply voltage as e.g. 8 V or higher.

Dimming mechanism

Application MFIO input signal can be a DC voltage or a pulse width modulated digital signal for dimming of the LED current.

1. Pure DC dimming: input voltage V_{MFIO} at pin MFIO. Continuous dimming from 3% dimming level up to 100% is embedded into a 100% ceiling plateau and an hysteresis range to off. Static dimming to a fixed value can be done via the resistor R_{set} .

Functional description

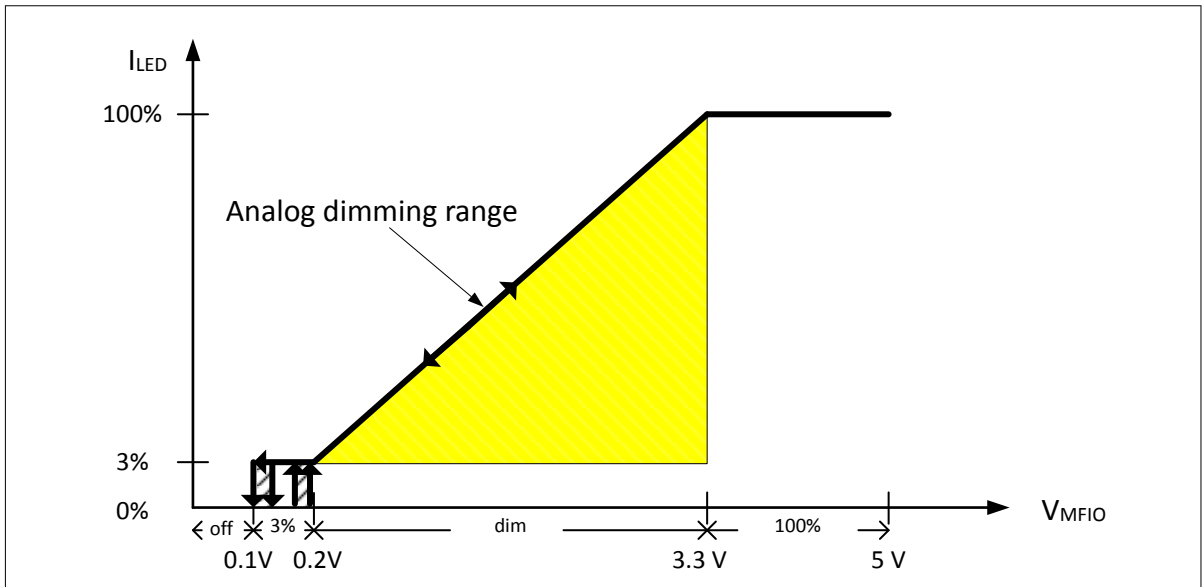


Figure 4 DC dimming

2. Pure PWM dimming: The PWM duty cycle at pin MFIO defines the dimming level. The PWM voltage amplitude corresponding to LED on must be in the voltage range specified by $V_{MFIO,100\%}$ and PWM voltage amplitude corresponding to LED off must be in the voltage range specified by $V_{MFIO,off}$. The LED current is PWM modulated according to the PWM input signal.
3. For resistive dimming using R_{set} and internal MFIO current, the internal pull-down has to be taken into account. For proper dimensioning refer to [Figure 5](#).

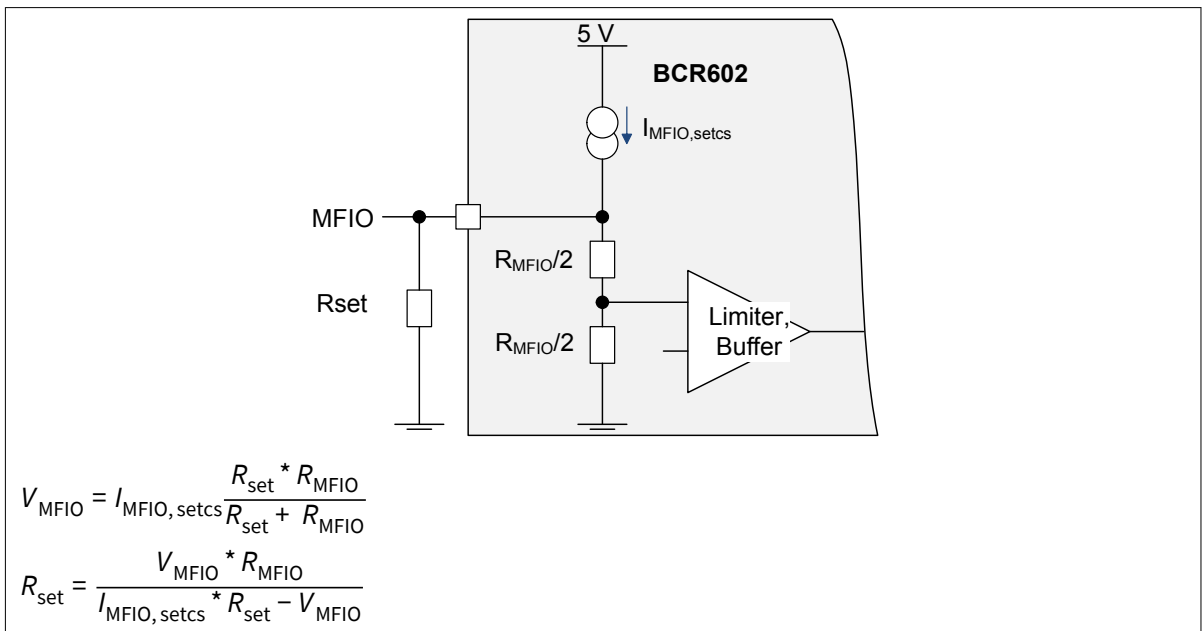


Figure 5 R_{set} dimensioning for resistor dimming

- $R_{MFIO,typical} = 285 \text{ k}\Omega$,
- $I_{MFIO,setcs,typical} = 20 \text{ }\mu\text{A}$.

Thermal characteristics

3 Thermal characteristics

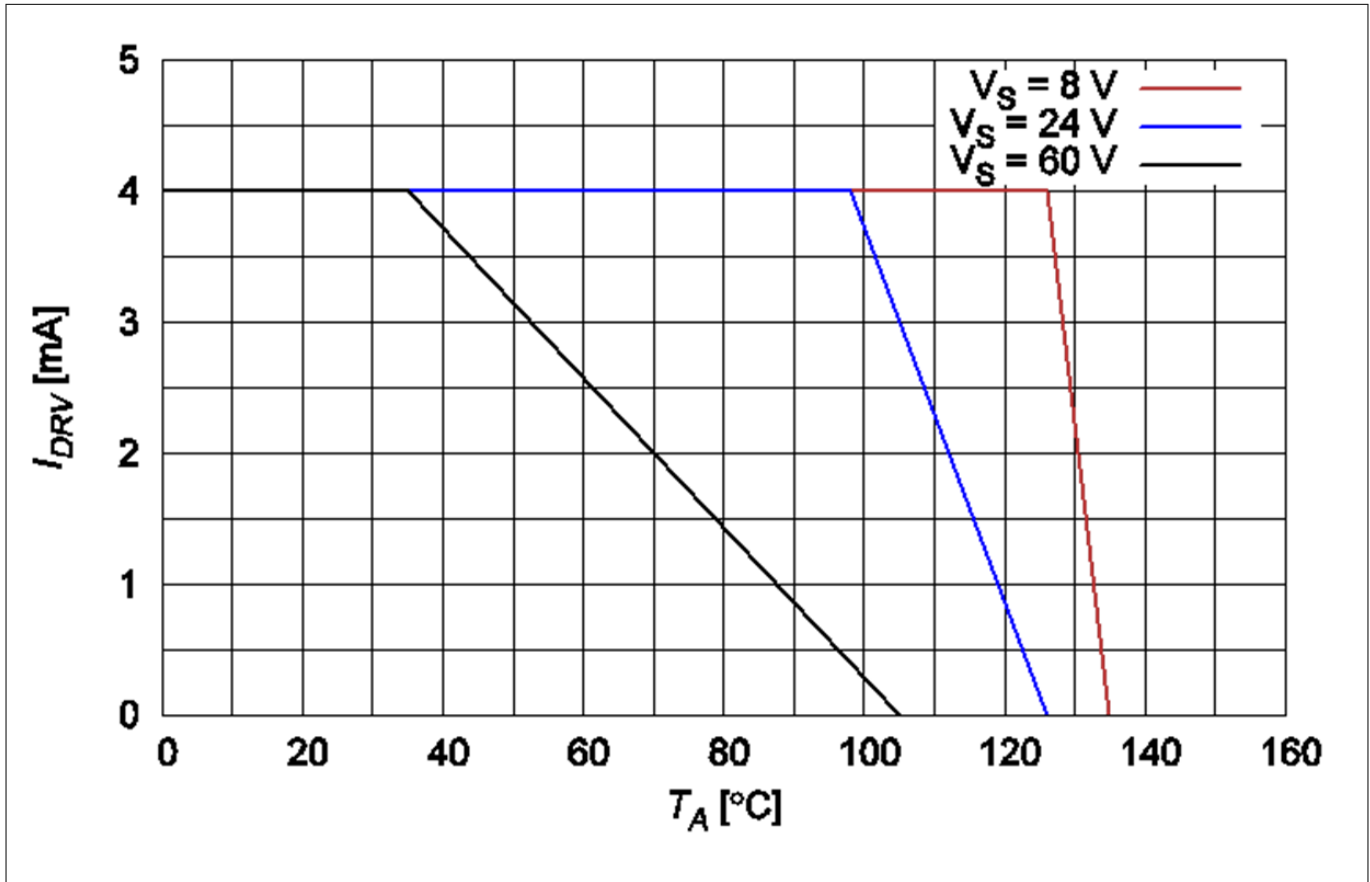


Figure 6 Maximum permitted effective output source current out of pin DRV into external driver transistor for a design example of 4 mA DC driver

The maximum permitted effective driver source current shown in [Figure 6](#) can be calculated by following equation:

$$I_{DRV} = \frac{\frac{T_{OTP, on, min} - T_A}{R_{thJA}} - V_S \cdot I_S}{V_S} = \frac{T_{OTP, on, min} - T_A}{V_S \cdot R_{thJA}} - I_S$$

The equation considers the power dissipation caused by the current consumption of the IC itself. If the driver current exceeds the calculated threshold the lower spec limit of the overtemperature protection will be exceeded and OTP might be triggered.

$T_{OTP, on, min}$ The lower spec limit of the overtemperature protection threshold should not be exceeded to avoid triggering the OTP.

Absolute maximum ratings

4 Absolute maximum ratings

Table 3 Absolute maximum ratings

| Parameter | Symbol | Values | | | Unit | Note or test condition |
|------------------------------------|---------------|--------|------|------|------|--|
| | | Min. | Typ. | Max. | | |
| Junction temperature | T_J | -40 | – | 160 | °C | – |
| Supply voltage | V_S | 0 | – | 65 | V | – |
| Input voltage at pin <i>MFIO</i> | V_{MFIO} | 0 | – | 5.0 | V | – |
| Input voltage at pin <i>VSENSE</i> | V_{sense} | 0 | – | 3.6 | V | – |
| Power dissipation | P_{tot} | – | – | 360 | mW | $V_S = 60\text{ V}$, $I_S = 2\text{ mA}$, $I_{DRV} = -4\text{ mA}$ |
| ESD robustness | $V_{ESD,HBM}$ | – | – | 2 | kV | HBMacc. to JEDEC JS-001 |
| | $V_{ESD,CDM}$ | – | – | 500 | V | CDM acc. to JEDEC JS-002 |

Attention: Stresses above the maximum values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Maximum ratings are absolute ratings. Exceeding only one of these values may cause irreversible damage to the integrated circuit.

Table 4 Maximum thermal resistance

| Parameter | Symbol | Values | | | Unit | Note or test condition |
|--|----------------|--------|------|------|------|--|
| | | Min. | Typ. | Max. | | |
| Thermal resistance junction to ambient | R_{thJA} | – | – | 290 | K/W | JEDEC 1s0p (JESD 51-3) footprint w/o extra cooling area |
| | $R_{thJA,100}$ | – | – | 200 | K/W | JEDEC 1s0p (JESD 51-3) with 100 mm ² cooling area |
| | $R_{thJA,300}$ | – | – | 180 | K/W | JEDEC 1s0p (JESD 51-3) with 300 mm ² cooling area |

Operating conditions**5 Operating conditions****Table 5 Operating conditions**

| Parameter | Symbol | Values | | | Unit | Note or test condition |
|----------------------|--------|--------|------|------|------|------------------------|
| | | Min. | Typ. | Max. | | |
| Junction temperature | T_J | -40 | - | 160 | °C | - |
| Supply voltage | V_S | 0 | - | 60 | V | - |

Electrical characteristics

6 Electrical characteristics

Note: All parameters are measured at $T_A = 25^\circ\text{C}$, $V_S = 45\text{ V}$ unless otherwise specified.

Note: $I_{\text{LED,target}}$ current is the undimmed current at a V_{SENSE} voltage drop of 400 mV typical.

Table 6 DC characteristics

| Parameter | Symbol | Values | | | Unit | Note or test condition |
|--------------------------------------|---|--------|------|-------|---------------|--|
| | | Min. | Typ. | Max. | | |
| IC system | | | | | | |
| Supply voltage | V_S | 8 | – | 60 | V | Operational supply voltage range |
| Supply voltage brownin | $V_{S,bi}$ | – | – | 8 | V | – |
| Supply voltage brownout | $V_{S,bo}$ | 6.7 | – | – | V | – |
| Supply current | I_S | -2.2 | – | – | mA | $I_{\text{DRV, source}} = 0\text{ A}$ |
| Sense voltage | V_{sense} | 388 | 400 | 412 | mV | Closed loop reference voltage of pin V_{SENSE} , $I_{\text{LED}} = V_{\text{sense}} / R_{\text{sense}}$ |
| LED current accuracy | | | | | | |
| LED current accuracy | $I_{\text{LED, acc}} / I_{\text{LED, acc, target}}$ | -3 | – | 3 | % | Closed loop LED current accuracy without dimming at $V_{\text{MFIO}} = 3.3\text{ V}$ |
| Driver | | | | | | |
| Driver source current capability, DC | $I_{\text{DRV, source}}$ | 10 | – | – | mA | Source current range of pin DRV to drive NPN base/NMOS gate |
| Driver sink current capability, DC | $I_{\text{DRV, sink}}$ | – | – | -10 | mA | Sink current range of pin DRV to discharge NPN base/NMOS gate |
| Driver source voltage | V_{DRV} | 4.5 | 5 | 5.5 | V | Max. output voltage of pin DRV |
| Dimming analog | | | | | | |
| MFIO turn-off range | $V_{\text{MFIO, off}}$ | 0 | – | 0.1 | V | Threshold for analog dimming to off |
| MFIO turn-on range | $V_{\text{MFIO, on}}$ | 0.17 | – | 0.195 | V | Threshold for analog dimming to on |
| MFIO full current range | $V_{\text{MFIO, 100\%}}$ | 3.3 | – | 5 | V | MFIO range always at 100% I_{LED} |
| MFIO output source current | $I_{\text{MFIO, setcs}}$ | 18 | 20 | 22 | μA | For $R_{\text{SET}} < 10\text{ k}\Omega$, in parallel internal pull-down R_{MFIO} connected, refer to Figure 5 |
| MFIO output voltage | $V_{\text{MFIO, setcs}}$ | – | 4.2 | – | V | MFIO output voltage at MFIO open |

Electrical characteristics
Table 6 DC characteristics (continued)

| Parameter | Symbol | Values | | | Unit | Note or test condition |
|--|--|--------|------|------|------------|--|
| | | Min. | Typ. | Max. | | |
| MFIO pull-down resistor | R_{MFIO} | 228 | 285 | 342 | k Ω | Internal pull-down resistor at pin <i>MFIO</i> |
| MFIO dimming range | $V_{MFIO, dim}$ | 0.2 | – | 3.3 | V | Analog dimming range of the LED current |
| Analog LED dimming | $I_{LEDmin, ana} / I_{LEDmin, target}$ | – | 3 | – | % | Minimum dimming LED current level at $MFIO_{dim} = 0.15 V$ |
| LED current chip to chip variation at selected dimming level | | -20 | – | 20 | % | Max variation at minimum MFIO dimming level |
| | | -10 | | 10 | | Max variation for dimming level higher than minimum |

Dimming PWM¹⁾

| | | | | | | |
|------------------------|-------------------------------------|-----|---|-----|---------|---|
| MFIO PWM frequency | f_{PWM} | – | – | 3.5 | kHz | Maximum supported PWM frequency at pin <i>MFIO</i> , external switch $Q_g = 8.7 nC$ |
| Minimum PWM duty cycle | $I_{LEDmin, PWM} / I_{LED, target}$ | – | 1 | – | % | Minimum LED current dimming ratio by a PWM signal connected to pin <i>MFIO</i> , external switch $Q_g = 8.7 nC$ |
| Minimum pulse width | $t_{duty, on}$ | 2.9 | – | – | μs | Minimum LED PWM digital pulse width between 0 V and 3.3 V, external switch $Q_g = 8.7 nC$ |

Overtemperature protection OTP

| | | | | | | |
|--|----------------|-----|---|-----|-------------|---|
| Overtemperature protection threshold, turn on | $T_{OTP, on}$ | 140 | – | 155 | $^{\circ}C$ | Junction threshold temperature to trigger overtemperature protection in standby, $I_{DRV} = 0 mA$ and $VS = 45 V$ |
| Overtemperature protection threshold, turn off | $T_{OTP, off}$ | 120 | – | 135 | $^{\circ}C$ | Junction threshold temperature to exit overtemperature protection in standby, $I_{DRV} = 0 mA$ and $VS = 45 V$ |

¹ Tested at 0.5 kHz and 3.5 kHz.

Electrical characteristics
Table 6 DC characteristics (continued)

| Parameter | Symbol | Values | | | Unit | Note or test condition |
|---------------------------------------|--|--------|------|------|------|--|
| | | Min. | Typ. | Max. | | |
| Sense voltage in OTP case | $V_{\text{sense, OTP}} / V_{\text{sense, target}}$ | – | 30 | – | % | Reduction factor at pin <i>VSENSE</i> (nominal 400 mV) if OTP has been triggered, $I_{\text{LED, OTP}} = V_{\text{sense, OTP}} / R_{\text{sense}}$ |
| Overtemperature protection hysteresis | $T_{\text{OTP, Hys}}$ | – | 20 | – | °C | – |
| Hot plug | | | | | | |
| Hot plug <i>VSENSE</i> threshold | $V_{\text{sense, HP}}$ | – | 8 | – | mV | <i>VSENSE</i> level at which hot plug event is detected |

Package information

7 Package information

Note: Dimensions in mm.

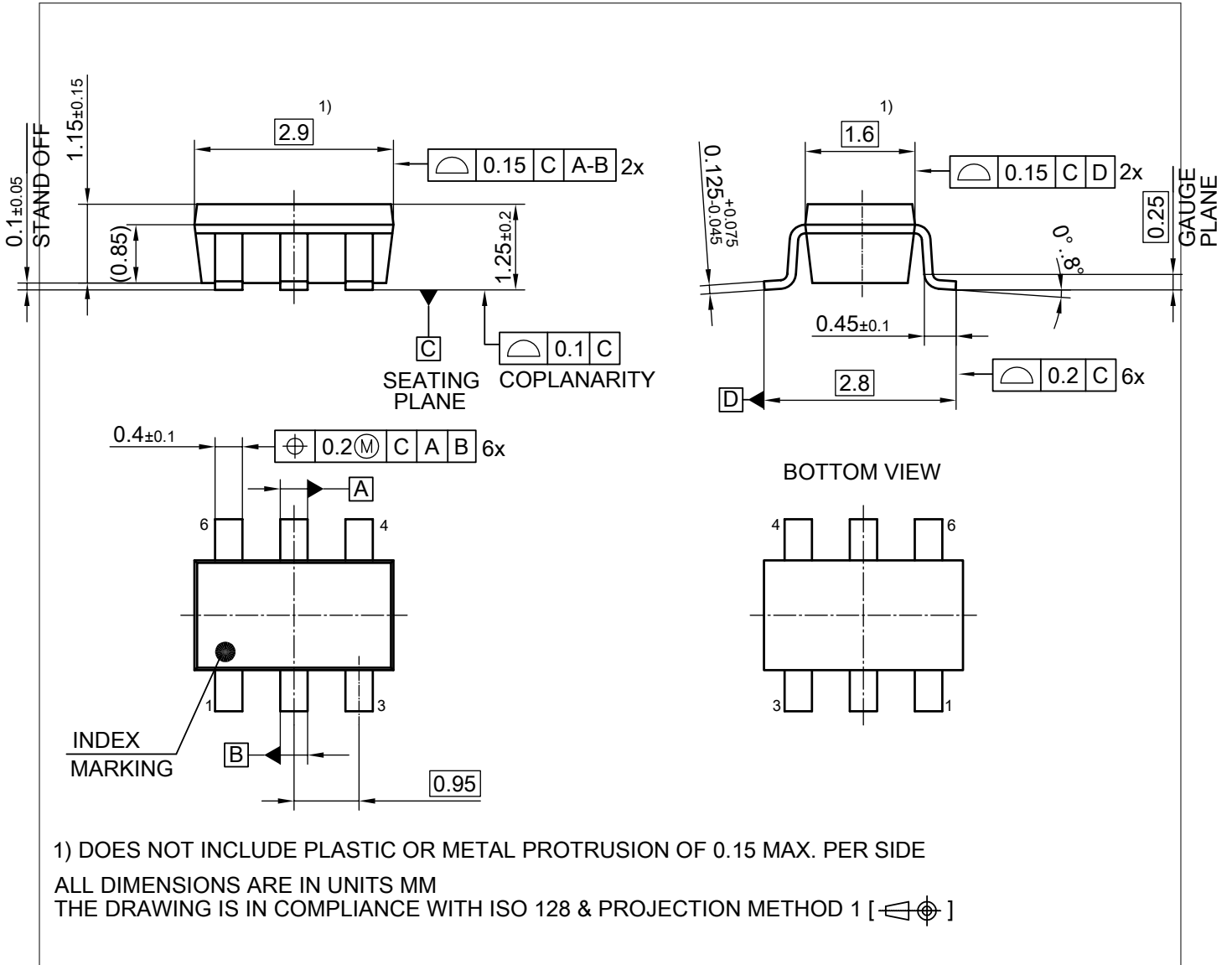


Figure 7 Package outline PG-SOT23-6

References

8 References

Revision history

| Document version | Date of release | Description of changes |
|------------------|-----------------|--|
| v1.0 | 2018-11-23 | <ul style="list-style-type: none">Public release |
| v1.1 | 2018-12-03 | <ul style="list-style-type: none">Parameter update |

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Edition 2018-12-3

Published by
Infineon Technologies AG
81726 Munich, Germany

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Document reference
IFX-rjb1519293082418

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